L	Hits	Search Text	DB	Time stamp
Number				
1	2184	(multilevel or multilayer or multi-level or	USPAT;	2004/08/20
		multi-layer or (multiple adj layer) or	US-PGPUB;	22:52
		(multiple adj level)) and tft and (active adj	EPO; JPO;	
		matrix)	DERWENT;	
	i		IBM_TDB	
2	4433	(plurality or multilevel or multilayer or	USPAT;	2004/08/20
		multi-level or multi-layer or (multiple adj	US-PGPUB;	22:53
		layer) or (multiple adj level)) and tft and	EPO; JPO;	
		(active adj matrix) and TiN	DERWENT;	
			IBM_TDB	
3	132	(plurality or multilevel or multilayer or	USPAT;	2004/08/20
		multi-level or multi-layer or (multiple adj	US-PGPUB;	22:54
		layer) or (multiple adj level)) and ((thin adj	EPO; JPO;	
		film adj transistor) or tft).ti,ab,clm. and	DERWENT;	
		(active adj matrix).ti,ab,clm. and ((titanium	IBM_TDB	
		adj nitride) or TiN).ti,ab,clm.		
4	31	(plurality or multilevel or multilayer or	USPAT;	2004/08/20
•		multi-level or multi-layer or (multiple adj	US-PGPUB;	22:55
		layer) or (multiple adj level)) and ((thin adj	EPO; JPO;	22.00
		film adj transistor) or tft).ti,ab,clm. and	DERWENT;	_
		(active adj matrix).ti,ab,clm. and ((titanium	IBM_TDB	
•		adj nitride) or TiN).ti,ab,clm. and (scan or	1811,188	
		scanning).ti,ab,clm.		
5	29	(plurality or multilevel or multilayer or	USPAT;	2004/08/20
•	23	multi-level or multi-layer or (multiple adj	US-PGPUB;	22:56
		layer) or (multiple adj level)) and ((thin adj	EPO; JPO;	22:30
		film adj transistor) or tft).ti,ab,clm. and	DERWENT;	
		(active adj matrix).ti,ab,clm. and ((titanium	IBM_TDB	
		adj nitride) or TiN).ti,ab,clm. and ((scan or	10.11.00	
		scanning) near2 line).ti,ab,clm.		
6	4	((thin adj film adj transistor) or	USPAT;	2004/08/20
	-	tft).ti,ab,clm. same (active adj	US-PGPUB;	22:58
		matrix).ti,ab,clm. same ((titanium adj	EPO; JPO;	£2.50
		nitride) or TiN).ti,ab,clm. same ((scan or	DERWENT;	
		scanning) near2 line).ti,ab,clm.	IBM_TDB	
7	3	((thin adj film adj transistor) or	USPAT;	2004/08/20
-		tft).ti,ab,clm. same (active adj	US-PGPUB;	2014/05/20
		matrix).ti,ab,clm. same ((titanium adj	· ·	22.30
		nitride) or TiN).ti,ab,clm. same ((scan or	EPO; JPO; DERWENT;	
		scanning) near2 line).ti,ab,clm. and hillock	IBM_TDB	
8	4	((thin adj film adj transistor) or	USPAT;	2004/08/20
	-	tft).ti,ab,clm. and (active adj	US-PGPUB;	23:03
		matrix).ti,ab,clm. and ((titanium adj nitride)	EPO; JPO;	£3;U3
		or TiN).ti,ab,clm. and ((tranium adj nitride)		
		near2 line).ti,ab,clm. and hillock	DERWENT;	
9	108		IBM_TDB	2004/09/20
•	100	((three near (level or layer))) near10 (ti or	USPAT;	2004/08/20
		titanium) near10 (aluminum or al) near10 (tin or (titanium adj nitride))	US-PGPUB;	23:04
		tim or tritamium auj mitrige);	EPO; JPO;	
			DERWENT;	
			IBM_TDB	

10	40	((three near (level or layer))) near10 (ti or	USPAT;	2004/08/20
		titanium) near10 (aluminum or al) near10	US-PGPUB;	23:12
		(tin or (titanium adj nitride)) and (tft or (thin	EPO; JPO;	
		near film near transistor))	DERWENT;	
		,	IBM_TDB	
11	40	((three near (level or layer))) near10 (ti or	USPAT;	2004/08/20
		titanium) near10 (aluminum or al) near10	US-PGPUB;	23:11
		(tin or (titanium adj nitride)) and (tft or (thin	EPO; JPO;	20111
		near film near transistor))	DERWENT;	
		near min hear translatory	IBM_TDB	
12	22	((three near (level or layer))) near10 (ti or	USPAT;	2004/08/20
'-		titanium) near10 (aluminum or al) near10		23:12
		·	US-PGPUB;	23:12
		(tin or (titanium adj nitride)) and (tft or (thin	EPO; JPO;	
		near film near transistor)) and (scan or	DERWENT;	
40		scanning)	IBM_TDB	2004/20100
13	2	((three near (level or layer))) near10 (ti or	USPAT;	2004/08/20
		titanium) near10 (aluminum or al) near10	US-PGPUB;	23:12
		(tin or (titanium adj nitride)) and (tft or (thin	EPO; JPO;	
		near film near transistor)) and (scan or	DERWENT;	
		scanning) and (nitrogen near concentration)	IBM_TDB	
14	17	(((three near (level or layer))) near10 (ti or	USPAT;	2004/08/20
		titanium) near10 (aluminum or al) near10	US-PGPUB;	23:13
		(tin or (titanium adj nitride)) and (tft or (thin	EPO; JPO;	
		near film near transistor))) and (ti or	DERWENT;	
l		titanium).ti,ab,clm.	IBM_TDB	
15	11	(((three near (level or layer))) near10 (ti or	USPAT;	2004/08/20
		titanium) near10 (aluminum or al) near10	US-PGPUB;	23:13
		(tin or (titanium adj nitride)) and (tft or (thin	EPO; JPO;	
		near film near transistor))) and (ti or	DERWENT;	
		titanium).ti,ab,clm. and (tin or (titanium adj	IBM_TDB	
		nitride)).ti,ab,clm.		
16	10	(((three near (level or layer))) near10 (ti or	USPAT;	2004/08/20
		titanium) near10 (aluminum or al) near10	US-PGPUB;	23:14
		(tin or (titanium adj nitride)) and (tft or (thin	EPO; JPO;	
		near film near transistor))) and (ti or	DERWENT;	
		titanium).ti,ab,clm. and (tin or (titanium adj	IBM_TDB	
		nitride)).ti,ab,clm. and (al or		
	_	aluminum).ti,ab,clm.		
17	9	(((three near (level or layer))) near10 (ti or	USPAT;	2004/08/20
	<b>j</b>	titanium) near10 (aluminum or al) near10	US-PGPUB;	23:14
		(tin or (titanium adj nitride)) and (tft or (thin	EPO; JPO;	
		near film near transistor))) and (ti or	DERWENT;	
		titanium).ti,ab,clm. same (tin or (titanium	IBM_TDB	
		adj nitride)).ti,ab,clm. same (al or		
40	_	aluminum).ti,ab,clm.		
18	6	(((three near (level or layer))) near10 (ti or	USPAT;	2004/08/20
		titanium) near10 (aluminum or al) near10	US-PGPUB;	23:20
		(tin or (titanium adj nitride)) and (tft or (thin	EPO; JPO;	
		near film near transistor))) and (ti or	DERWENT;	
		titanium).ti,ab,clm. near10 (tin or (titanium	IBM_TDB	
		adj nitride)).ti,ab,clm. near10 (al or		
	<u> </u>	aluminum).ti,ab,clm.		

19	1	(((three near (level or layer))) near10 (ti or	USPAT;	2004/08/20
		titanium) near10 (aluminum or al) near10	US-PGPUB;	23:20
		(tin or (titanium adj nitride)) and (tft or (thin	EPO; JPO;	
		near film near transistor))) and (ti or	DERWENT;	
		titanium).ti,ab,clm. near10 (tin or (titanium	IBM_TDB	
		adj nitride)).ti,ab,clm. near10 (al or	_	
		aluminum).ti,ab,clm. and (nitrogen near		
		concentration)		